



# KI SEMICONDUCTOR CO.

## SOT-23 Plastic-Encapsulate Diodes

**1SS184**

SWITCHING DIODE

### FEATURES

Power dissipation

$$P_D : 150 \text{ mW} (T_{amb}=25^\circ\text{C})$$

Forward Current

$$I_F : 100 \text{ mA}$$

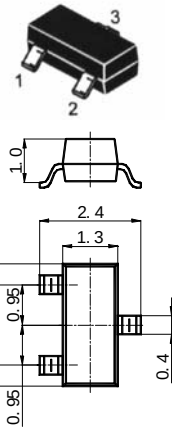
Reverse Voltage

$$V_R : 80 \text{ V}$$

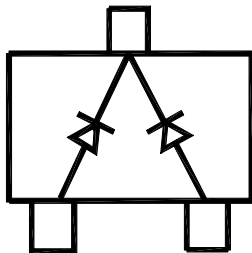
Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$

**SOT-23**



Unit: mm



Marking B3

### ELECTRICAL CHARACTERISTICS( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

| Parameter                       | Symbol     | Test conditions                     | MIN | MAX | UNIT          |
|---------------------------------|------------|-------------------------------------|-----|-----|---------------|
| Reverse breakdown voltage       | $V_{(BR)}$ | $I_R = 100\mu\text{A}$              | 80  |     | V             |
| Reverse voltage leakage current | $I_R$      | $V_R = 80\text{V}$                  |     | 0.5 | $\mu\text{A}$ |
| Forward voltage                 | $V_F$      | $I_F = 100\text{mA}$                |     | 1.2 | V             |
| Diode capacitance               | $C_D$      | $V_R = 0\text{V}$ $f = 1\text{MHz}$ |     | 3   | pF            |
| Reverse recovery time           | $t_{rr}$   |                                     |     | 4   | nS            |